

WHAT IS CLAIMED IS

1. A plasma etching apparatus comprising:
 - a lower electrode supporting a semiconductor substrate;
 - 5 a focus ring disposed along a circumference of said semiconductor substrate;
 - a sensor for measuring a position of an upper surface of said focus ring;
 - 10 a drive mechanism for driving said focus ring vertically; and
 - 15 a controller for adjusting the position of the upper surface of said focus ring by driving said drive mechanism on the basis of a result of measurement by said sensor.
2. The plasma etching apparatus according to claim 1,
 - 15 wherein said sensor can measure the position of the upper surface of said focus ring at a plurality of points of said focus ring, and
 - 20 said drive mechanism can change the position of the upper surface of said focus ring at a plurality of points of said focus ring.
3. A plasma etching method comprising:
 - 25 a measurement step of measuring an upper surface of a focus ring;
 - an adjustment step of adjusting a position of the upper surface of the focus ring by driving the focus ring vertically on the basis of the result of measurement by said measurement step; and
 - 30 an etching step of performing etching after finishing said adjustment step.
4. The plasma etching method according to claim 3,

wherein said measurement step includes a step of measuring the upper surface of the focus ring at a plurality of points of the focus ring, and

5 said adjustment step includes a step of adjusting the position of the upper surface of the focus ring at a plurality of points of the focus ring on the basis of the result of measurement by said measurement step.